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PTO/SB/21	(08-03)
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DEMARKE TRAN			Applic	ation Number	10/017,033		
			Filing	Date	December 14, 2001		
F	FORM		First N	lamed Inventor	M'Saad, Hichem		
(to be used for all co	rrespondence after ini	tial filing)	Art Un	nit	1731		
			Exami	ner Name	Hoffmann, John M.		
Total Number of Page Submission	es in This		Attorn	ey Docket Number	A6139/T43800		
		ENC	OSURE	S (Check all that apply	()		
Fee Transmittal F	orm	Drawin	g(s)		After Allowance Communication to Group		
Fee Attache	ed	Licensi	ng-relate	ed Papers	Appeal Communication to Board of Appeals and Interferences		
Amendment/Rep	ly.	Petition) -		Appeal Communication to Group (Appeal Notice, Brief, Reply Brief)		
After Final			n to Convert to a onal Application		Proprietary Information		
Affidavits/de	eclaration(s)	Power of Attorney, Revocation Change of Correspondence Address			Status Letter		
Extension of Time Request		Terminal Disclaimer		Other Enclosure(s) (please identify below):			
Express Abandonment Request =		_ ·	lest for Refund		Copies of two (2) cited references Return Postcard		
Certified Copy of Priority Document(s) Re		Remai	The Commissioner is authorized to charge any additional fees to Deposits Account 20-1430.				
Response to Missing Parts/ Incomplete Application			.				
Response to Missing Parts under 37 CFR 1.52 or 1.53							
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT							
Firm or	Townsend and Townsend and Crew LLP						
Individual	Patrick M. Bouche	· · · · · · · · · · · · · · · · · · ·		Reg. No	o. 44,037		
Signature Patali Re-							

CERTIFICATE OF TRANSMISSION/MAILING

I hereby certify that this correspondence is being facsimile transmitted to the USPTO or deposited with the United States Postal Service with sufficient postage as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on the date shown below.

Typed or printed name Nina L. McNeill

Signature Turn J. McNeill

Date June 30, 2004

Daté

June 30, 2004

PTO/SB/17 (10-03) Complete if Known FEE TRANSMITTAL 10/017,033 **Application Number** for FY 2004 December 14, 2001 Filing Date Effective 10/01/2003. Patent fees are subject to annual revision. M'Saad, Hichem First Named Inventor Applicant claims small entity status. See 37 CFR 1.27 Hoffmann, John M. Examiner Name 1731 Art Unit TOTAL AMOUNT OF PAYMENT (\$) A6139/T43800 Attorney Docket No.

$\overline{}$	METHOD OF PAYMENT (check all that apply)				FEE CA	ALCULATION (continued)	
Check	Credit Card Money Order Other None	3. ADD	ITIONAL I	FEES		·	
Deposit Acc		Large	Entity	Small	Entity		
Deposit Account	20-1430	Fee Code	Fee (\$)	Fee Code	Fee (\$)	Fee Description	Fee Paid
Number	20-1430	1051	130	2051	65	Surcharge - late filing fee or oath	
		1052	50	2052	25	Surcharge - late provisional filing fee or	
Deposit Account	Townsend and Townsend and Crew LLP	1				cover sheet.	
Name	Townsend and Townsend and Crew LLF	1053	130	1053	130	Non-English specification	<u> </u>
The Director is	authorized to: (check all that apply)	1812 1804	2,520	1812	2,520	For filing a request for reexamination	
Charge fée(s) indicated below Credit any overpayments	1804	920*	1804	920*	Requesting publication of SIR prior to Examiner action	
Charge any	additional fee(s) or any underpayment of fee(s)	1805	1,840*	1805	1,840*	Requesting publication of SIR after Examiner action	
	s) indicated below, except for the filing fee	1251	110	2251	EE	•	
to the above-ide	ntified deposit account.	1251	110 420	2251 2252	55 210	Extension for reply within first month	
	FEE CALCULATION	1'232	720	2252	210	Extension for reply within second month	
	LING FEE	1253	950	2253	475	Extension for reply within third month	
Large Entity	Small Entity	1254	1,480	2254	740	Extension for reply within fourth month	
Fee Fee Code (\$)	Fee Fee Fee Description Fee Paid Code (\$)			l			
***	2001 385 Utility filing fee	1255	2,010	2255	1,005	Extension for reply within fifth month	<u> </u>
	2002 170 Design filing fee	1401	330	2401	165	Notice of Appeal	<u> </u>
1003 530	2003 265 Plant filing fee	1402	330	2402	165	Filing a brief in support of an appeal	<u> </u>
1004 770	2004 385 Reissue filing fee	1403	290	2403	145	Request for oral hearing	
1005 160	2005 80 Provisional filing fee	1451	1,510	1451	1,510	Petition to institute a public use proceeding	
	SUBTOTAL (1) (\$)	1452	110	2452	55	Petition to revive – unavoidable	
		1453	1,330	2453	665	Petition to revive – unintentional	
2. EXTRA CI	AIM FEES FOR UTILITY AND REISSUE	1501	1,330	2501	665	Utility issue fee (or reissue)	
	Fee from	1502	480	2502	240	Design issue fee	
L	Extra Claims below Fee Paid	1503	640	2503	320	Plant issue fee	
Total Claims		1460	130	1460	130	Petitions to the Commissioner	
Independent Claims	-·· = =	1807	50	1807	50	Petitions related to provisional applications	
Multiple L.	× E	1806	180	1806	180	Submission of Information Disclosure Stmt	180
Dependent Large Entity Fee Fee	Small Entity Fee Fee	8021	40	8021	40	Recording each patent assignment per property (times number of properties)	
Code (\$)	Code (\$) Fee Description	1809	770	2809	385	Filing a submission after final rejection (37 CFR § 1.129(a))	
1202 18 1201 86	2202 9 Claims in excess of 20 2201 43 Independent claims in excess of 3	1810	770	2810	385	For each additional invention to be	
1203 290	2203 145 Multiple dependent claim, if not paid					examined (37 CFR § 1.129(b)) Request for Continued Examination	
1204 86	2204 43 ** Reissue independent claims over original patent	1801	770	2801	385	(RCE)	
1205 18	2205 9 ** Reissue claims in excess of 20 and over original patent	1802	900	1802	900	Request for expedited examination of a design application	
	SUBTOTAL (2) (\$)	Other fe	e (specify)			***************************************	
**or number prev	ously paid, if greater; For Reissues, see above						
		Reduce	a by Basic	: Filing F	ee Paid	SUBTOTAL (3) (\$)180	Ī

SUBMITTED BY	,			Con	nplete (if applicable)
Name (Print/Type)	Patrick M. Boucher	Registration No. (Attorney/Agent)	44,037	Telephone	303-571-4000
Signature	Patilia			Date	June 30, 2004

PATENT

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to:

Attorney Docket No.: A6139/T43800 AMAT No.: 006139/DD/HDP/CVD/JW TTC No.: 016301-043800US

ommissioner for Patent

D. Box 1450

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TOWNSEND AND TOWNSEND AND CREW LLP

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of:

Hichem M'Saad

Application No.: 10/017,033

Filed: December 14, 2001

For: HDP-CVD FILM FOR

UPPERCLADDING APPLICATION IN

OPTICAL WAVEGUIDES

Examiner: Hoffmann, John M.

Art Unit: 1731

SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT UNDER 37

CFR §1.97 and §1.98

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

The references cited on attached form PTO/SB/08A and PTO/SB/08B are being called to the attention of the Examiner. Copies of the references are enclosed.

It is respectfully requested that the cited references be expressly considered during the prosecution of this application, and the references be made of record therein and appear among the "references cited" on any patent to issue therefrom.

The following translations of the abstracts of these references are provided, and constitute the entire understanding of the relevance of the references as understood by the

Hichem M'Saad

Application No.: 10/017,033

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undersigned. No English translation of the entire references is known to be available to any individual specified in 37 C.F.R. §1.56(c).

1. EP 0 659 902

Plasma-assisted CVD of a silica thin film on a substrate involves: (a) introducing oxygen and opt. argon into a vacuum chamber, igniting the plasma and then introducing silane; and (b) carrying out the process under the conditions of 40-80 (pref. 60) microbars gas pressure in the chamber, 0-35 (pref. 10) cu.cm/min. argon supply rate, 12-24 (pref. 12) cu.cm/min. silane supply rate, 13-38 (pref. 26-38) cu.cm/min. oxygen supply rate, 200-300 (pref. 200) deg.C substrate temp. and 750-1100 (pref. 1100) W plasma reactor power. Phosphine may also be introduced into the chamber to dope the silica thin film.

Also claimed in an appts. for carrying out silica thin film CVD.

USE - E.g. in the prodn. of a planar optical waveguide on a silicon substrate or in the mfr. of a flat LCD screen

ADVANTAGE - The process alows deposition of silica contg. very little hydrogen (10-100 ppm) at close to 200 deg.C and produces 0.1-10 microns thick deposits in a few mins.

2. EP 0 735 160

In a process for CVD of a silica thin film, for an integrated optical waveguide, from O2 and SiCl4 with microwave-generated plasma assistance, the novelty is that: (a) the substrate temp. is maintained at 200-800 (pref. 500-600) deg.C; (b) the CVD chamber pressure is maintained at 1-20 Pa; and (c) the SiCl4-contg. reactive gas is injected between the plasma and the substrate within the chamber. Pref. the plasma is created from O2 and the ractive gas also contains a carrier gas and opt. one or more dopants such as GeCl4, C2F6, POCl3 and/or BCl3.

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Also claimed are: (i) a CVD appts. for carrying out the above process; and (ii) an integrated

optical waveguide mfg. method including the above process.

ADVANTAGE - The process produces a thin film with improved thickness and

optical index uniformity, while maintaining high deposition rate, a reduced number of process

steps and a low process tem. (< 800 deg.C). Additionally, the thin film has acceptable optical

attenuation at 1.55 and 1.3 mum, without the need for a supplementary annealing step.

As provided for by 37 CFR 1.97(g) and (h), no inference should be made that the

information and references cited are prior art merely because they are in this statement and no

representation is being made that a search has been conducted or that this statement encompasses

all the possible relevant information.

This IDS is being filed before the mailing date of the final Office Action or

Notice of Allowance.

Please charge the IDS fee of \$180 to Deposit Account No. 20-1430. Please

deduct any additional fees from, or credit any overpayment to, the above-noted Deposit Account.

Respectfully submitted,

Patrick M. Boucher

Patok ga

Reg. No. 44,037

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PMB:pmb

60228943 v1

PTO/SB/08B (08-03) TRADENE Substitute for form 1449B/PTO Complete if Known 10/017,033 Application Number **INFORMATION DISCLOSURE** Filing Date December 14, 2001 STATEMENT BY APPLICANT First Named Inventor M'Saad, Hichem Art Unit 1731 (use as many sheets as necessary) Hoffmann, John M. Examiner Name 016301-043800US Sheet Attorney Docket Number

FOREIGN PATENT DOCUMENTS								
Examiner Initials*	Cite No. ¹	For	eign Patent Docume Number ⁴ _{Kinc}	nt I Code ^s (<i>if known</i>)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T ⁶ .
	Y	EP	0 659 902	A1	28-6-1995	France Telecom		
	Z	EP	0 735 160	B1	30-8-2000	France Telecom		
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Examiner	Date	
Signature	Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Applicant's unique citation designation number (optional). Applicant is to place a check mark here if English language Translation is attached.